

CMSN3134KDW-HF

Dual N-Channel
RoHS Device
Halogen Free



Features

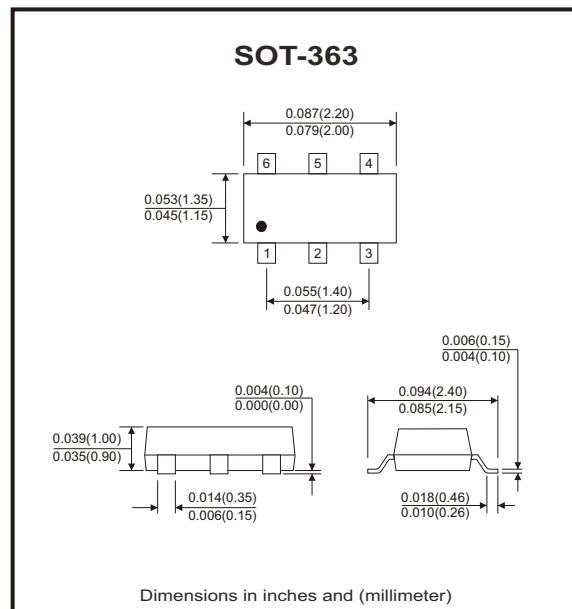
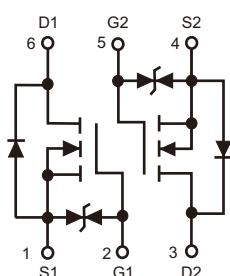
- Surface mount package.
- N-Channel switch with Low RDS(on).
- Operated at low logic level gate drive.

Mechanical data

- Case: SOT-363, molded plastic.
- Mounting position: Any.

Circuit Diagram

G : Gate
S : Source
D : Drain



Maximum Ratings (at Ta=25 °C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V _{DS}	20	V
Typical gate-source voltage	V _{GS}	±12	V
Continuous drain current (t ≤ 10s)	I _D	0.75	A
Power dissipation (Note 1)	P _D	0.15	W
Thermal resistance from junction to ambient	R _{θJA}	833	°C/W
Operating junction temperature range	T _J	-55 to +150	°C
Storage temperature range	T _{STG}	-55 to +150	°C

Notes: 1. Repetitive rating: Pulse width limited by junction temperature.

Electrical Characteristics (at $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 10\text{V}, V_{\text{DS}} = 0\text{V}$			± 20	μA
Gate threshold voltage (Note 1)	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\mu\text{A}$	0.35	0.54	1.1	V
Drain-source on-state resistance (Note 1)	$R_{\text{DS(on)}}$	$V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 0.65\text{A}$		270	380	$\text{m}\Omega$
		$V_{\text{GS}} = 2.5\text{V}, I_{\text{D}} = 0.55\text{A}$		320	450	
		$V_{\text{GS}} = 1.8\text{V}, I_{\text{D}} = 0.45\text{A}$		390	800	
Forward transconductance (Note 1)	g_{fs}	$V_{\text{DS}} = 10\text{V}, I_{\text{D}} = 0.8\text{A}$		1.6		S
Drain forward voltage (Note 1)	V_{SD}	$I_{\text{S}} = 0.15\text{A}, V_{\text{GS}} = 0\text{V}$			1.2	V
Dynamic characteristics (Note 2)						
Input capacitance	C_{iss}	$V_{\text{DS}} = 16\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		79	120	pF
Output capacitance	C_{oss}			13	20	
Reverse transfer capacitance	C_{rss}			9	15	
Switching characteristics (Note 2)						
Turn-on delay time	$t_{\text{d(on)}}$	$V_{\text{GS}} = 4.5\text{V}, V_{\text{DS}} = 10\text{V}$ $I_{\text{D}} = 0.5\text{A}, R_{\text{GEN}} = 10\Omega$		6.7		nS
Turn-on rise time	t_{r}			4.8		
Turn-off delay time	$t_{\text{d(off)}}$			17.3		
Turn-off fall time	t_{f}			7.4		
Total gate charge	Q_{g}	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 0.25\text{A}$		750		pC
Gate-source charge	Q_{gs}			75		
Gate-drain charge	Q_{gd}			225		

Notes: 1. Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 0.5\%$.

2. Guaranteed by design, not subject to production.

Typical Rating and Characteristic Curves (CMSON3134KDW-HF)

Fig.1 - Output Characteristics

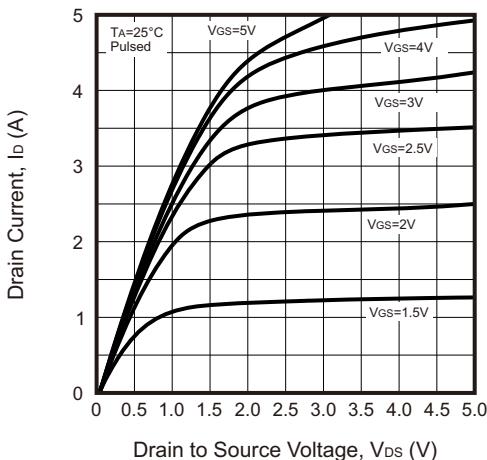


Fig.2 - Transfer Characteristics

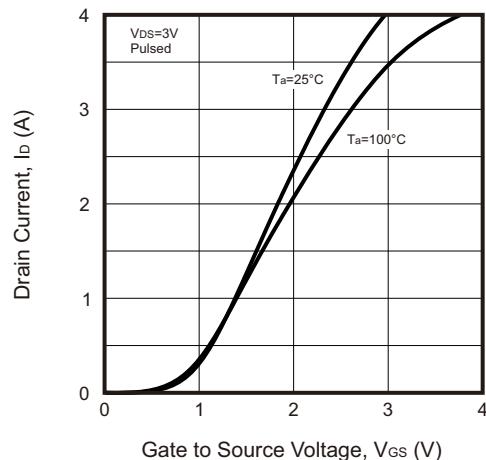


Fig.3 - $R_{DS(ON)}$ — I_D

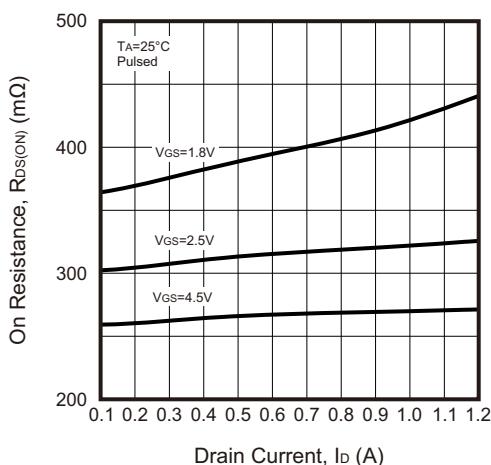


Fig.4 - On-Resistance vs. Gate to Source Voltage

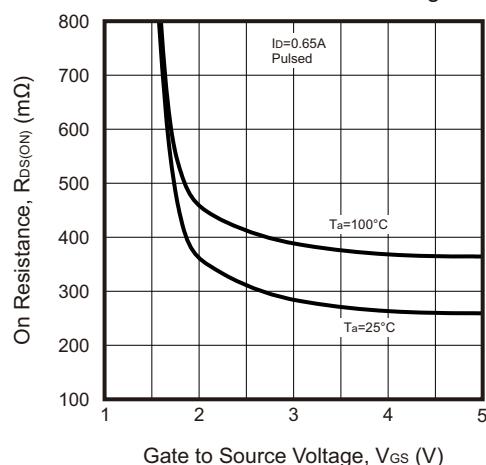


Fig.5 - I_S — V_{SD}

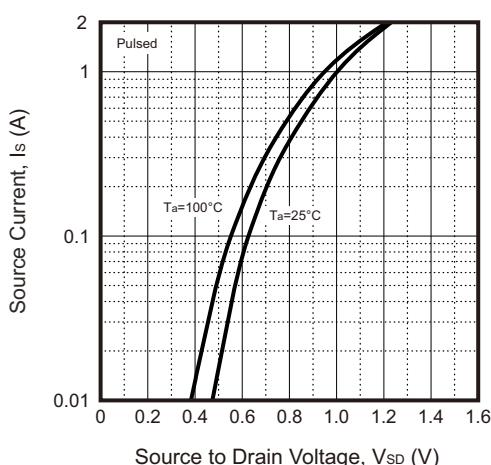
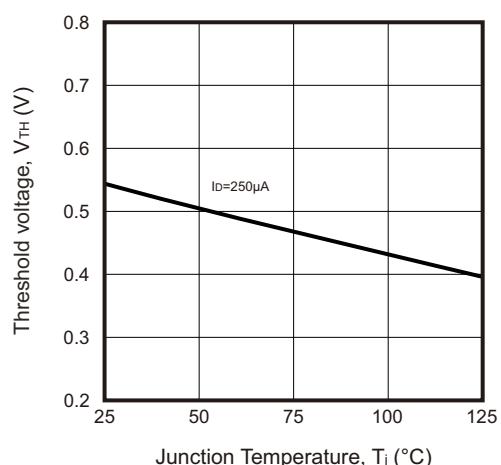
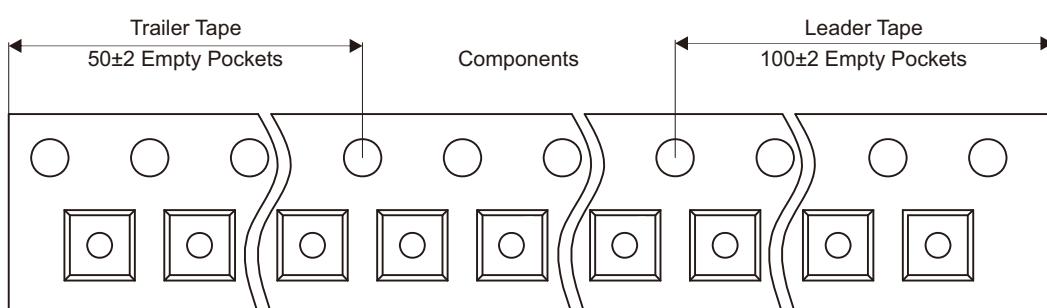
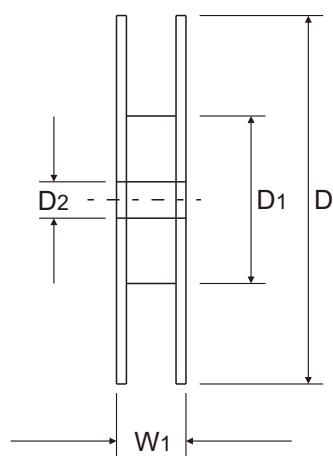
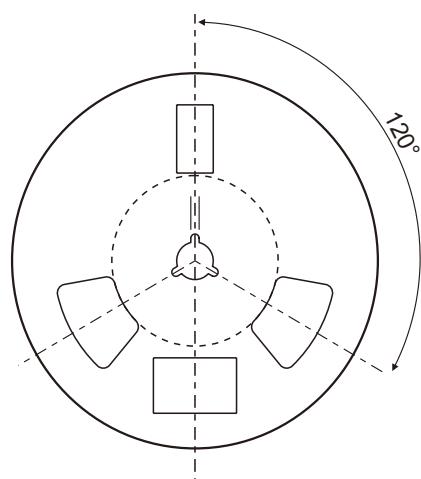
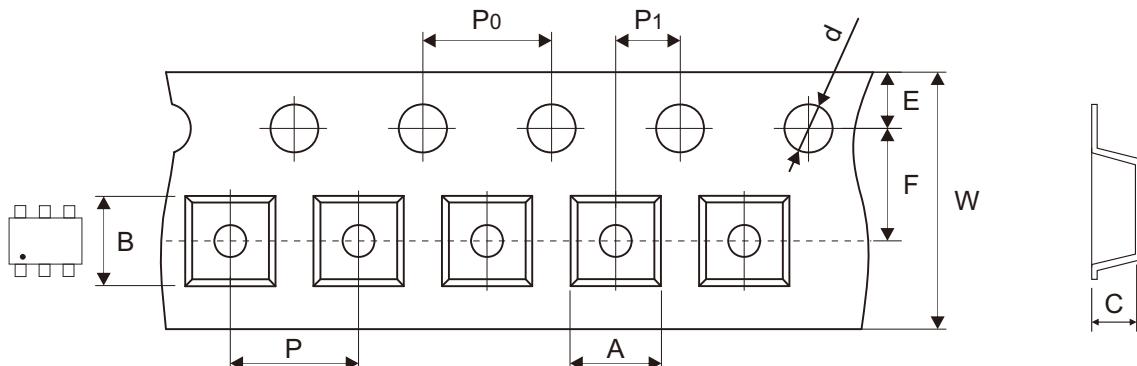


Fig.6 - Threshold Voltage



Reel Taping Specification

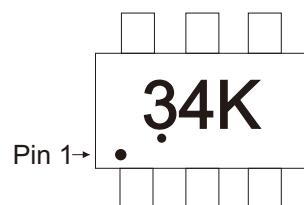


	SYMBOL	A	B	C	d	D	D ₁	D ₂
SOT-363	(mm)	2.25 ± 0.13	2.55 ± 0.10	1.20 ± 0.10	$1.50 + 0.10$ $- 0.00$	178.00 ± 0.10	54.40 ± 0.40	13.00 ± 0.20
	(inch)	0.089 ± 0.005	0.100 ± 0.004	0.047 ± 0.004	$0.059 + 0.004$ $- 0.000$	7.008 ± 0.004	2.142 ± 0.016	0.512 ± 0.008

	SYMBOL	E	F	P	P ₀	P ₁	W	W ₁
SOT-363	(mm)	1.75 ± 0.10	3.50 ± 0.10	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.05	$8.00 + 0.30$ $- 0.10$	12.30 ± 1.00
	(inch)	0.069 ± 0.004	0.138 ± 0.004	0.157 ± 0.004	0.157 ± 0.004	0.079 ± 0.002	$0.315 + 0.012$ $- 0.004$	0.484 ± 0.039

Marking Code

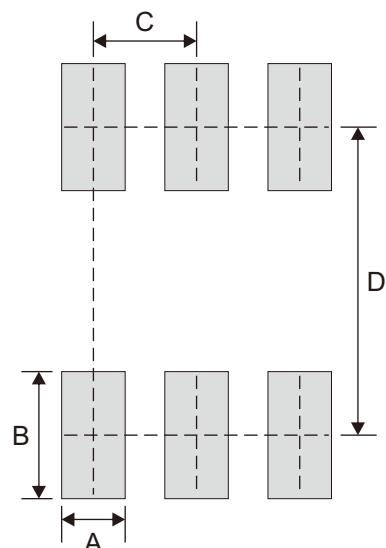
Part Number	Marking Code
CMSN3134KDW-HF	34K



Solid dot = Control code

Suggested P.C.B. PAD Layout

SIZE	SOT-363	
	(mm)	(inch)
A	0.40	0.016
B	0.80	0.031
C	0.65	0.026
D	1.94	0.076



Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
SOT-363	3,000	7